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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	09/649,569
Filing Date	AUGUST 28, 2000
First Named Inventor	PATEL et AFCFIVED
Group Art Unit	1746
Examiner Name	Unknown AN 0 2001

Sheet of Attorney Docket Number P06-US

			_	U.S. PATENT DOCU	IMENTS	
Examiner Cite		U.S. Patent Doo		Name of Patentee or Applicant	Date of Publication of	Pages, Columns, Lines,
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Application Number	09/649,569	
Filing Date	AUGUST 28, 2	000
First Named Inventor	PATEL et al.	MECENTER
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	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	_
Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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EH	Assorted promotional literature, Surface Technology Systems Ltd., Newport, UK (July 28, 1999)	
	EA EB EC ED EE	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, sympositum, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. EA STRELLER et al., "Selectivity in Dry Etching of Si(100) and XeF2 and VUV Light", Elsevier Science B.V., Applied Surface Science, (1996), 106: pp. 341-346 EB VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5), (Sep/Oct 1996), pp. 2766-2774 EC WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", Transducers '97, 1997 International Conference on Solid-State Sensors and Actuators, Chicago (June 16-19), pp. 1505-1508 ED WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Science Technology B 1(4), (Oct-Dec 1983), pp. 927-931 EE WINTERS et al., "The Etching of Silicon with XeF2 Vapor", Appl. Phys. Lett. 34(1), January 1, 1979, pp. 70-73. Ef GILDEMEISTER, J.M., "Xenon Difluoride Etching System", (Nov 17, 1997) "Xenon Difluoride Isotropic Etch System", Seeing is Believing, Surface Technology Systems Ltd. brochure, Newport, UK (date unknown) Assorted promotional literature. Surface Technology Systems Ltd., Newport, UK (July 28, 1999)

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Examiner Initials*	Cite No.1	U.S. Patent D	Nocument Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Sheet 2 of 2

Co	mplete if Kno	own
Application Number	09/649,569	(PE)
Hing Date	AUGUST 28.	3600
First Named Inventor	PATEL et al.	16
Group Art Unit	1746	NOV 2 9 2000 PM
Examiner Name	Unknown	
Attorney Docket Number	P06-US	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Complete if Known Substitute for form 1449A/PTO 09/649,569 **Application Number** INFORMATION DISCLOSURE **AUGUST 28, 2000** Filing Date STATEMENT BY APPLICANT PATEL et al. **First Named Inventor** 1746 Art Unit (use as many sheets as necessary) PURNELL. A. Examiner Name Sheet 1 of Attorney Docket Number **P06-US**

			U.S. PATI	ENT DOCUMENTS	
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³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3).

⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

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Complete if Known Substitute for form 1449A/PTO **Application Number** 09/649.569 INFORMATION DISCLOSURE **AUGUST 28. 2000** Filing Date First Named Inventor STATEMENT BY APPLICANT PATEL et al. 1746 **Art Unit** (use as many sheets as necessary) PURNELL. A **Examiner Name** Sheet of Attorney Docket Number **P06-US**

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AND	GW	JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
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